

/ Descriptions

Silicon NPN transistor in a SOT-23 Plastic Package.

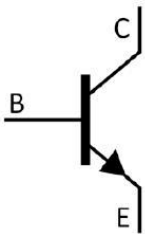
/ Features

High I_C , high h_{FE} .

/ Applications

Use in audio output driver stage amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	300~550	500~700	650~1000
Marking	H28B	H28C	H28D

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	1.0	A
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	20			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ $I_C=0$	6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=40V$ $I_E=0$			1.0	μA
Emitter Cut-Off Current	I_{CEO}	$V_{CE}=20V$ $I_B=0$			5.0	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1.0V$ $I_C=100mA$	300		1000	
	$h_{FE(2)}$	$V_{CE}=1.0V$ $I_C=500mA$	300			
	$h_{FE(3)}$	$V_{CE}=1.0V$ $I_C=300mA$	300			
	$h_{FE(4)}$	$V_{CE}=1.0V$ $I_C=1.0mA$	290			

M28M

Rev.F Apr.-2017

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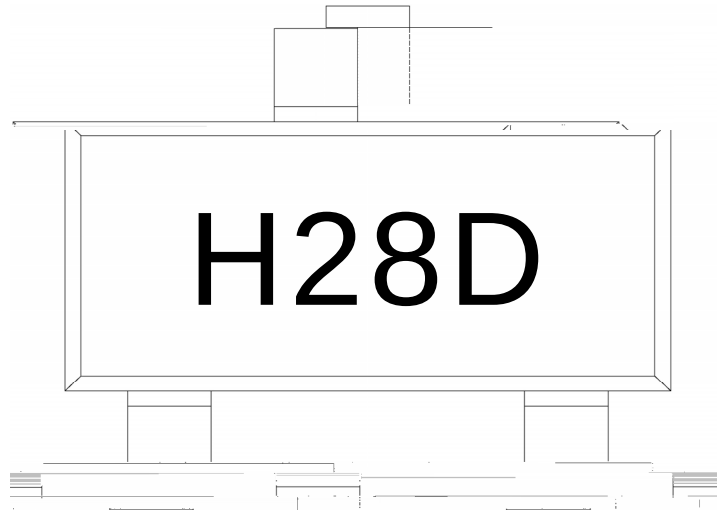
/ Package Dimensions

SOT-23

单位: mm



/ Marking Instructions



H

28

D h_{FE}

Note:

H: Company Code.

28: Product Type.

D: h_{FE} Classifications Symbol.

